

N-Channel 60 V (D-S) Super Junction Power MOSFET

PRODUCT SUMMARY		
V_{DS} (V)	$R_{DS(on)}$ (m Ω)(Typ.)	I_D (A) ^a (Max.)
60	2.5 at $V_{GS} = 10$ V	140

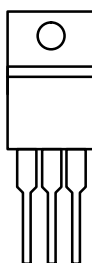
FEATURES

- 175 °C Junction Temperature
- Super Junction Power MOSFET
- Material categorization:

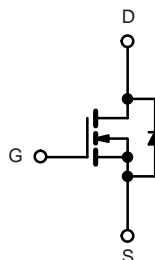


RoHS
COMPLIANT

TO-220



G D S
Top View



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS ($T_C = 25$ °C, unless otherwise noted)				
Parameter		Symbol	Limit	Unit
Gate-Source Voltage		V_{GS}	± 20	V
Continuous Drain Current ($T_J = 175$ °C) ^b	$T_C = 25$ °C	I_D	140	A
	$T_C = 100$ °C		116 ^a	
Pulsed Drain Current		I_{DM}	510	
Continuous Source Current (Diode Conduction)		I_S	120 ^a	
Avalanche Current		I_{AS}	137	
Single Avalanche Energy (Duty Cycle ≤ 1 %)	L = 0.1 mH	E_{AS}	650	mJ
Maximum Power Dissipation	$T_C = 25$ °C	P_D	208	W
	$T_A = 25$ °C		3.3 ^b , 9 ^b , c	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	- 55 to 175	°C

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^a	t ≤ 10 sec	R_{thJA}	13	18	°C/W
	Steady State		40	50	
Maximum Junction-to-Case		R_{thJC}	0.8	1.1	

Notes:

a. Package limited.

b. Surface mounted on 1" x 1" FR4 board.

c. t ≤ 10 s.

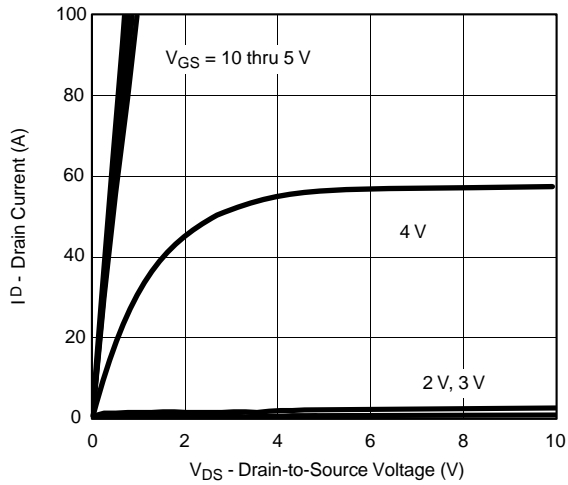
SPECIFICATIONS ($T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted)						
Parameter	Symbol	Test Conditions	Min.	Typ. ^a	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	60			V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	2		4	
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 60\text{ V}, V_{GS} = 0\text{ V}$			1	μA
		$V_{DS} = 48\text{ V}, V_{GS} = 0\text{ V}, T_J = 125\text{ }^\circ\text{C}$			50	
		$V_{DS} = 48\text{ V}, V_{GS} = 0\text{ V}, T_J = 175\text{ }^\circ\text{C}$			250	
On-State Drain Current ^b	$I_{D(on)}$	$V_{DS} = 5\text{ V}, V_{GS} = 10\text{ V}$	140			A
Drain-Source On-State Resistance ^b	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 20\text{ A}$		2.5	3.8	$\text{m}\Omega$
		$V_{GS} = 10\text{ V}, I_D = 20\text{ A}, T_J = 125\text{ }^\circ\text{C}$		3.0	4.8	
		$V_{GS} = 10\text{ V}, I_D = 10\text{ A}, T_J = 175\text{ }^\circ\text{C}$		4.0	5.9	
Forward Transconductance ^b	g_{fs}	$V_{DS} = 48\text{ V}, I_D = 20\text{ A}$		58		S
Dynamic						
Input Capacitance	C_{iss}	$V_{GS} = 0\text{ V}, V_{DS} = 30\text{ V}, f = 1\text{ MHz}$		8550		pF
Output Capacitance	C_{oss}			1270		
Reverse Transfer Capacitance	C_{rss}			42		
Total Gate Charge ^c	Q_g	$V_{DS} = 30\text{ V}, V_{GS} = 10\text{ V}, I_D = 20\text{ A}$		78	98	nC
Gate-Source Charge ^c	Q_{gs}			16		
Gate-Drain Charge ^c	Q_{gd}			9.5		
Turn-On Delay Time ^c	$t_{d(on)}$	$V_{DD} = 30\text{ V}, R_L = 0.6\text{ }\Omega$ $I_D \cong 20\text{ A}, V_{GEN} = 10\text{ V}, R_g = 2.5\text{ }\Omega$		10		ns
Rise Time ^c	t_r			5		
Turn-Off Delay Time ^c	$t_{d(off)}$			55		
Fall Time ^c	t_f			12		
Source-Drain Diode Ratings and Characteristics ($T_C = 25\text{ }^\circ\text{C}$)						
Pulsed Current	I_{SM}				140	A
Diode Forward Voltage	V_{SD}	$I_F = 20\text{ A}, V_{GS} = 0\text{ V}$		1	1.2	V
Reverse Recovery Time	t_{rr}	$I_F = 20\text{ A}, di/dt = 100\text{ A}/\mu\text{s}$		45	100	ns

Notes:

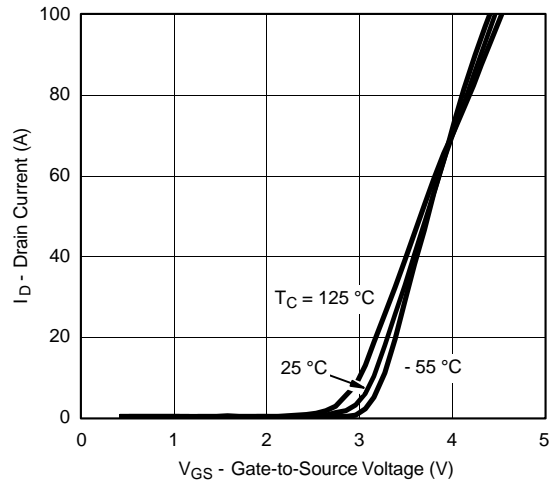
- For design aid only; not subject to production testing.
- Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
- Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

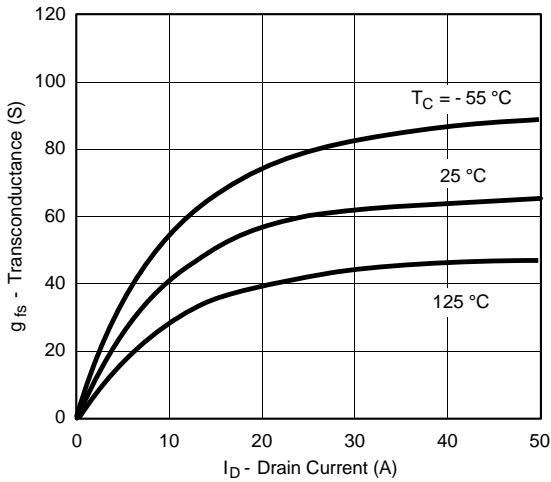
TYPICAL CHARACTERISTICS (25 °C unless noted)



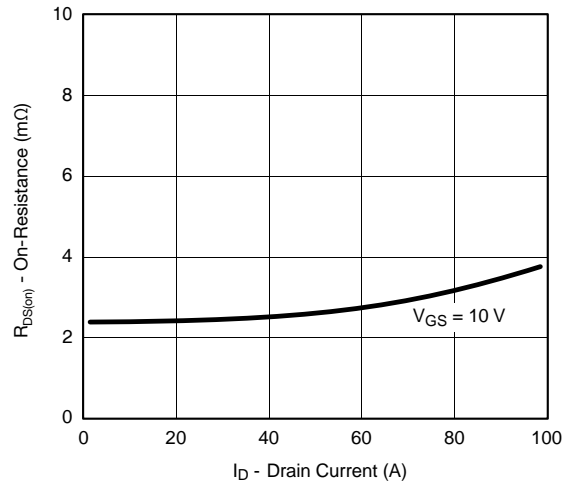
Output Characteristics



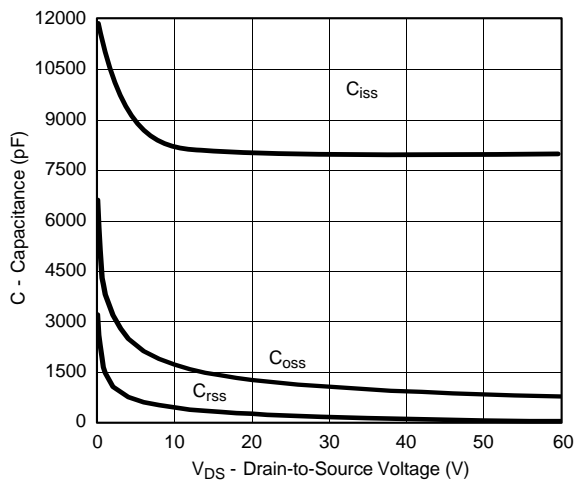
Transfer Characteristics



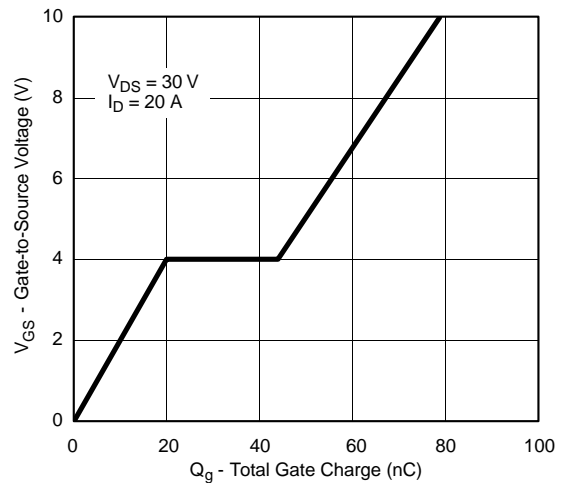
Transconductance



On-Resistance vs. Drain Current

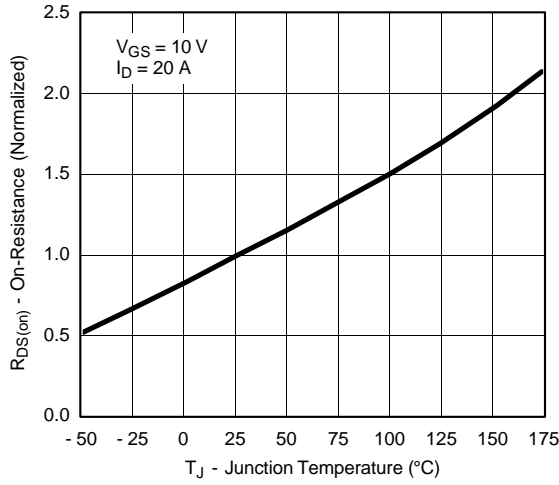


Capacitance

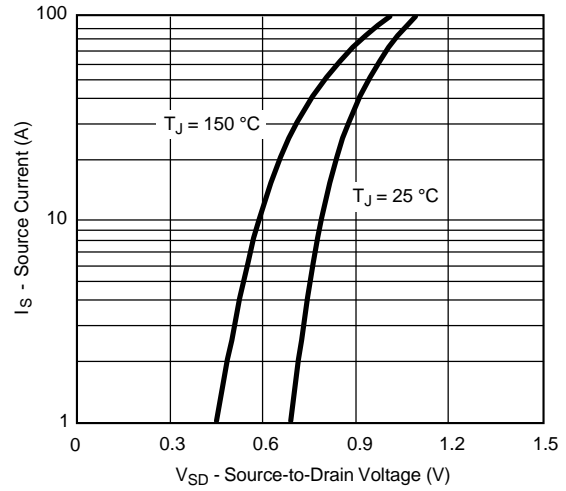


Gate Charge

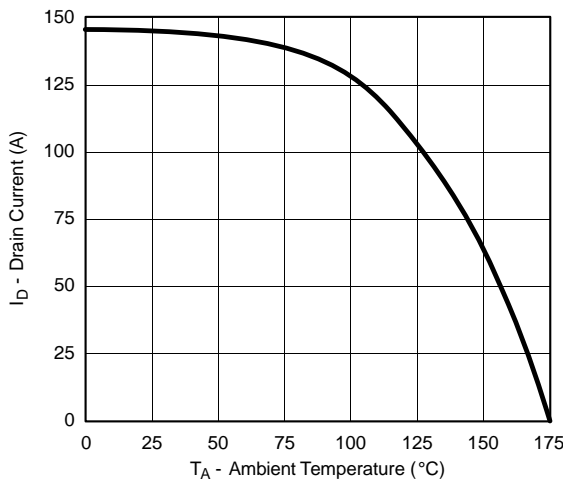
TYPICAL CHARACTERISTICS (25 °C unless noted)



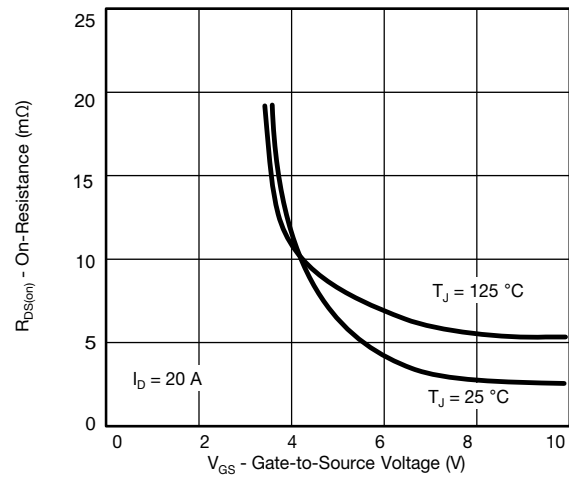
On-Resistance vs. Junction Temperature



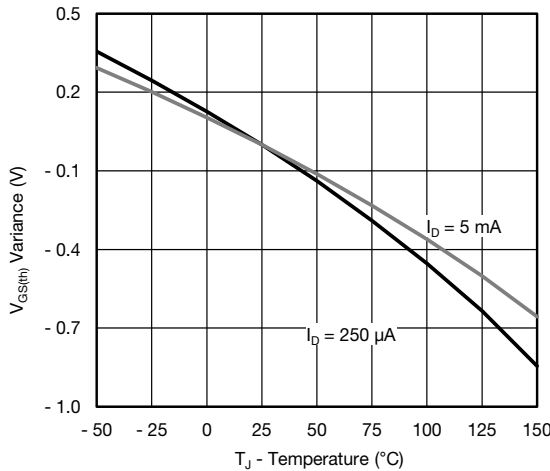
Source-Drain Diode Forward Voltage



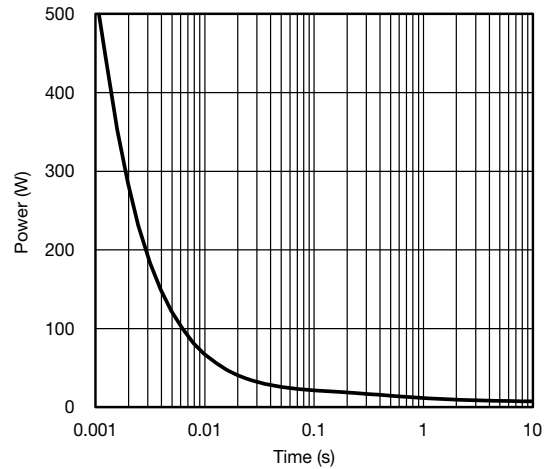
Maximum Drain Current vs. Ambient Temperature



On-Resistance vs. Gate-to-Source Voltage

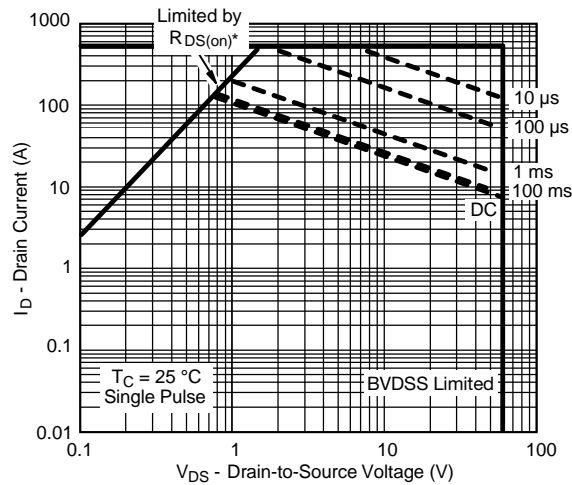


Threshold Voltage



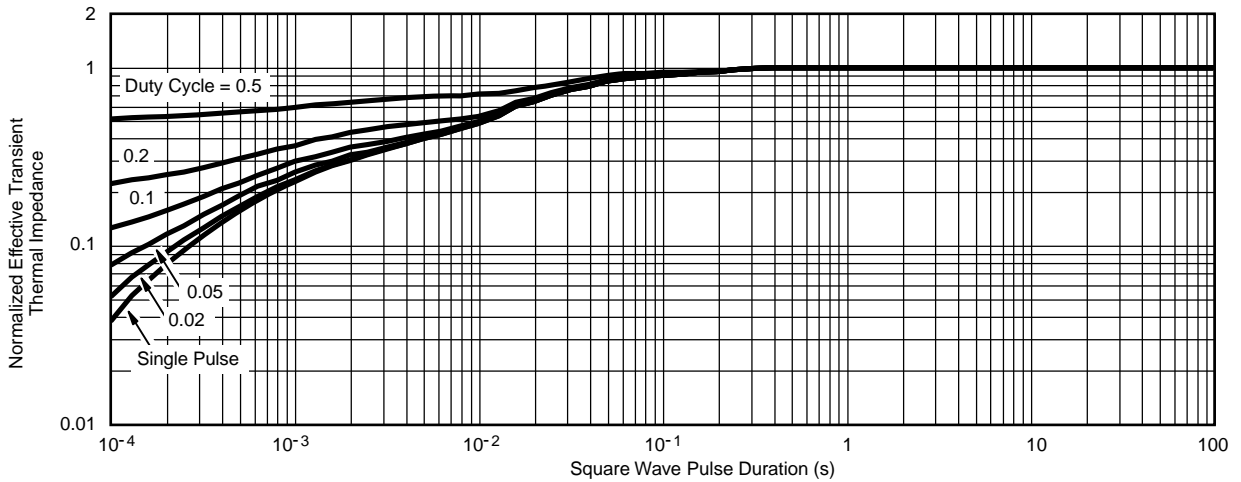
Single Pulse Power, Junction-to-Ambient

TYPICAL CHARACTERISTICS (25 °C unless noted)



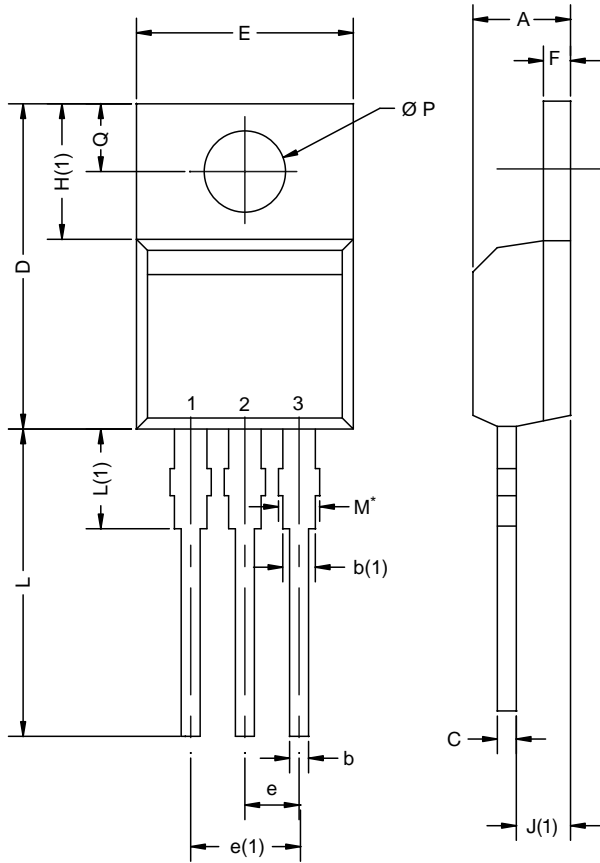
* $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified

Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Case

TO-220AB



DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	4.25	4.65	0.167	0.183
b	0.69	1.01	0.027	0.040
b(1)	1.20	1.73	0.047	0.068
c	0.36	0.61	0.014	0.024
D	14.85	15.49	0.585	0.610
E	10.04	10.51	0.395	0.414
e	2.41	2.67	0.095	0.105
e(1)	4.88	5.28	0.192	0.208
F	1.14	1.40	0.045	0.055
H(1)	6.09	6.48	0.240	0.255
J(1)	2.41	2.92	0.095	0.115
L	13.35	14.02	0.526	0.552
L(1)	3.32	3.82	0.131	0.150
$\varnothing P$	3.54	3.94	0.139	0.155
Q	2.60	3.00	0.102	0.118

ECN: X12-0208-Rev. N, 08-Oct-12
DWG: 5471

Notes

* M = 1.32 mm to 1.62 mm (dimension including protrusion)
Heatsink hole for HVM

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